

**1Mx4 Dynamic RAM
CMOS, Monolithic**

**ADVANCE INFORMATION
Features**

The EDI441024C is a fast page mode 4096K bit high performance, low power CMOS Dynamic RAM organized as 1024Kx4. The use of four-layer poly process, combined with silicide technology and a single transistor dynamic storage cell, provide high circuit density with high performance.

The use of dynamic circuitry, including sense amplifiers, assures low power dissipation.

Multiplexed address inputs permit a low pin count for maximum system density.

In addition to the RAS\ only refresh mode, the hidden refresh mode and CAS\ before RAS\ refresh mode are available.

All inputs and outputs are TTL compatible and operate from a single 5 volt supply.

Military product compliant to MIL-STD-883, paragraph 1.2.1, is available.

1Mx4 bit CMOS Dynamic
Random Access Memory

- Access Times 80, 100, 120, and 150ns
- Low Operating Power Dissipation
- Low Standby Power
- Common I/O
- All Inputs/Outputs TTL Compatible

Available in Two Package Styles

- 20 pin Ceramic ZIP, No.18
- 20(26) Lead Ceramic SOJ, No. 16

Single +5V ($\pm 10\%$) Supply Operation

Pin Names

A0-A9	Address Inputs
CAS\	Column Address Strobe
RAS\	Row Address Strobe
W\	Write Control Input
G\	Output Enable
DQ1-DQ4	Data Inputs/Outputs
VCC	Power (+5V $\pm 10\%$)

**Pin Configurations
and Block Diagram**

